Qingjiang Li

List of Publications by Year
in descending order

44 papers	684 citations
687363 13 h-index	580821 25 g-index
44 all docs	44 docs citations
44 times ranked	988 citing authors

#	Article	IF	Citations
1	Eliminating Negative‐SET Behavior by Suppressing Nanofilament Overgrowth in Cation‐Based Memory. Advanced Materials, 2016, 28, 10623-10629.	21.0	189
2	Short-Term and Long-Term Plasticity Mimicked in Low-Voltage Ag/GeSe/TiN Electronic Synapse. IEEE Electron Device Letters, 2018, 39, 492-495.	3.9	54
3	A Self-Rectification and Quasi-Linear Analogue Memristor for Artificial Neural Networks. IEEE Electron Device Letters, 2019, 40, 1407-1410.	3.9	42
4	A Ti/AlO$_x$/TaO$_x$/Pt Analog Synapse for Memristive Neural Network. IEEE Electron Device Letters, 2018, 39, 1298-1301.	3.9	41
5	Calibration strategy of the JUNO experiment. Journal of High Energy Physics, 2021, 2021, 1.	4.7	39
6	A Memristor SPICE Model Accounting for Synaptic Activity Dependence. PLoS ONE, 2015, 10, e0120506.	2.5	30
7	Coexistence of memory resistance and memory capacitance in TiO2 solid-state devices. Nanoscale Research Letters, 2014, 9, 552.	5.7	29
8	Threshold Switching Behavior of Ag-SiTe-Based Selector Device and Annealing Effect on its Characteristics. IEEE Journal of the Electron Devices Society, 2018, 6, 674-679.	2.1	26
9	A HfO2/SiTe Based Dual-Layer Selector Device with Minor Threshold Voltage Variation. Nanomaterials, 2019, 9, 408.	4.1	23
10	Impact of threshold voltage variation on 1S1R crossbar array with threshold switching selectors. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	20
11	Analysis of the Negative-SET Behaviors in Cu/ZrO2/Pt Devices. Nanoscale Research Letters, 2016, 11, 542.	5.7	18
12	A Configurable Artificial Neuron Based on a Threshold-Tunable TiN/NbOâ,"/Pt Memristor. IEEE Electron Device Letters, 2022, 43, 631-634.	3.9	17
13	The design and sensitivity of JUNOâ€™s scintillator radiopurity pre-detector OSIRIS. European Physical Journal C, 2021, 81, 1.	3.9	15
14	Highly improved resistive switching performances of the self-doped Pt/HfO2:Cu/Cu devices by atomic layer deposition. Science China: Physics, Mechanics and Astronomy, 2016, 59, 1.	5.1	13
15	Radioactivity control strategy for the JUNO detector. Journal of High Energy Physics, 2021, 2021, 1.	4.7	13
16	Understanding the conduction and switching mechanism of Ti/AlOx/TaOx/Pt analog memristor. Physics Letters, Section A: General, Atomic and Solid State Physics, 2019, 383, 125877.	2.1	11
17	JUNO sensitivity to low energy atmospheric neutrino spectra. European Physical Journal C, 2021, 81, 1.	3.9	11
18	Quasi-Analytical Model of 3-D Vertical-RRAM Array Architecture for MB-Level Design. IEEE Transactions on Electron Devices, 2017, 64, 1568-1574.	3.0	9

#	ARTICLE	IF	CITATIONS
19	Quaternary synapses network for memristor-based spiking convolutional neural networks. IEICE Electronics Express, 2019, 16, 20190004-20190004.	0.8	9
20	Memory Devices: Eliminating Negative-SET Behavior by Suppressing Nanofilament Overgrowth in Cation-Based Memory (Adv. Mater. 48/2016). Advanced Materials, 2016, 28, 10809-10809.	21.0	6
21	A TaO$_x$-Based Electronic Synapse With High Precision for Neuromorphic Computing. IEEE Access, 2019, 7, 184700-184706.	4.2	6
22	*In Situ* Learning in Hardware Compatible Multilayer Memristive Spiking Neural Network. IEEE Transactions on Cognitive and Developmental Systems, 2022, 14, 448-461.	3.8	6
23	Impact of active areas on electrical characteristics of TiO$_2$ based solid-state memristors. , 2015, , .		5
24	Exploration of selector characteristic based on electron tunneling for RRAM array application. IEICE Electronics Express, 2017, 14, 20170739-20170739.	0.8	5
25	Unidirectional threshold switching in Ag/Si-based electrochemical metallization cells for high-density bipolar RRAM applications. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	5
26	Voltage-control oscillator based on Pt/C/NbOx/TiN device with highly improved threshold switching performances. Science China: Physics, Mechanics and Astronomy, 2019, 62, 1.	5.1	4
27	Transition from rectification to resistive-switching in Ti/MgF2/Pt memory. AIP Advances, 2019, 9, 105117.	1.3	4
28	Enhanced Spiking Neural Network with forgetting phenomenon based on electronic synaptic devices. Neurocomputing, 2020, 408, 21-30.	5.9	4
29	A bidirectional threshold switching selector with a symmetric multilayer structure. Science China Information Sciences, 2021, 64, 1.	4.3	4
30	In-situ learning in multilayer locally-connected memristive spiking neural network. Neurocomputing, 2021, 463, 251-264.	5.9	4
31	A memristor random circuit breaker model accounting for stimulus thermal accumulation. IEICE Electronics Express, 2016, 13, 20160376-20160376.	0.8	3
32	Configurable activation function realized by non-linear memristor for neural network. AIP Advances, 2020, 10, 085207.	1.3	3
33	EEG Signal Epilepsy Detection System Based on Convolutional Neural Network and Memristor Array. , 2021, , .		3
34	A rate-adjustable true random number generator based on the stochastic delay of a TiN/NbOx/Pt memristor. AIP Advances, 2021, 11, .	1.3	3
35	High-Speed Real-Time Ion Detection System for Time-of-Flight Mass Spectrometry Application. Spectroscopy Letters, 2012, 45, 464-469.	1.0	2
36	Practical considerations of read-out circuits for passive, multi-level ReRAM arrays. , 2016, , .		2

#	Article	IF	Citations
37	Binary Memristive Synapse Based Vector Neural Network Architecture and Its Application. IEEE Transactions on Circuits and Systems II: Express Briefs, 2021, 68, 772-776.	3.0	2
38	Impact of electroforming polarity on TiO_2 based memristor. IEICE Electronics Express, 2016, 13, 20160613-20160613.	0.8	1
39	A compliance current circuit with nanosecond response time for ReRAM characterization. , 2017, , .		1
40	Analysis, Design, and Order Estimation of Least-Squares FIR Equalizers for Bandwidth Extension of ADCs. Circuits, Systems, and Signal Processing, 2019, 38, 2165-2186.	2.0	1
41	A Symmetric Multilayer GeSe/GeSeSbTe Ovonic Threshold Switching Selector with Improved Endurance and Stability. , 2021, , .		1
42	New write operation scheme for alleviating effect of line resistance on RRAM crossbar array. , 2016, , .		0
43	An FPGA-based manipulation system for ReRAM characterization. , 2016, , .		0
44	Network Pruning Towards Highly Efficient RRAM Accelerator. IEEE Nanotechnology Magazine, 2022, 21, 340-351.	2.0	0